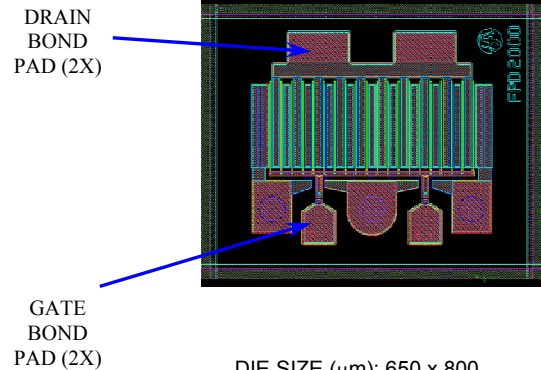


- **PERFORMANCE (1.8 GHz)**
 - ◆ 33 dBm Linear Output Power
 - ◆ 14.5 dB Power Gain
 - ◆ Useable Gain to 10 GHz
 - ◆ 44 dBm Output IP3
 - ◆ 20 dB Maximum Stable Gain
 - ◆ 45% Power-Added Efficiency
 - ◆ 10V Operation / Plated Source Thru-Vias



DIE SIZE (μm): 650 x 800
 DIE THICKNESS: 75 μm
 BONDING PADS (μm): >70 x 70

- **DESCRIPTION AND APPLICATIONS**

The FPD2000V is a discrete depletion mode AlGaAs/InGaAs pseudomorphic High Electron Mobility Transistor (pHEMT), optimized for power applications in L- and C-Bands. The FPD2000V includes Source plated thru-vias, and does not require wire bonds to the Source.

Typical applications include drivers or output stages in PCS/Cellular base station transmitter amplifiers, as well as other power applications in WLL/WLAN amplifiers.

- **ELECTRICAL SPECIFICATIONS AT 22°C**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
RF SPECIFICATIONS MEASURED AT $f = 1.8$ GHz USING CW SIGNAL						
Power at 1dB Gain Compression	P_{1dB}	$V_{DS} = 10V$; $I_{DS} = 350$ mA Γ_S and Γ_L tuned for Optimum IP3	32	33		dBm
Power Gain at dB Gain Compression	G_{1dB}	$V_{DS} = 10V$; $I_{DS} = 350$ mA Γ_S and Γ_L tuned for Optimum IP3	13.0	14.5		
Maximum Stable Gain S_{21}/S_{12}	MSG	$V_{DS} = 10$ V; $I_{DS} = 350$ mA $P_{IN} = 0$ dBm, 50 Ω system		20		dB
Power-Added Efficiency at 1dB Gain Compression	PAE	$V_{DS} = 10V$; $I_{DS} = 350$ mA Γ_S and Γ_L tuned for Optimum IP3		45		%
3 rd -Order Intermodulation Distortion Γ_S and Γ_L tuned for Optimum IP3	IM3	$V_{DS} = 10V$; $I_{DS} = 350$ mA $P_{OUT} = 22$ dBm (single-tone level)		-46		dBc
Saturated Drain-Source Current	I_{DSS}	$V_{DS} = 1.3$ V; $V_{GS} = 0$ V	975	1150	1375	mA
Maximum Drain-Source Current	I_{MAX}	$V_{DS} = 1.3$ V; $V_{GS} \cong +1$ V		1800		mA
Transconductance	G_M	$V_{DS} = 1.3$ V; $V_{GS} = 0$ V		1200		mS
Gate-Source Leakage Current	I_{GSO}	$V_{GS} = -3$ V		35	85	μ A
Pinch-Off Voltage	$ V_P $	$V_{DS} = 1.3$ V; $I_{DS} = 4$ mA	0.7	0.9	1.4	V
Gate-Source Breakdown Voltage	$ V_{BDGS} $	$I_{GS} = 4$ mA	6	8		V
Gate-Drain Breakdown Voltage	$ V_{BDGD} $	$I_{GD} = 4$ mA	20	22		V
Thermal Resistivity	Θ_{CC}	See Note on following page		18		$^{\circ}\text{C}/\text{W}$

• **RECOMMENDED OPERATING BIAS CONDITIONS**

Drain-Source Voltage: From 5V to 10V
 Quiescent Current: From 25% I_{DSS} to 55% I_{DSS}

• **ABSOLUTE MAXIMUM RATINGS¹**

Parameter	Symbol	Test Conditions	Min	Max	Units
Drain-Source Voltage	V _{DS}	-3V < V _{GS} < +0V		12	V
Gate-Source Voltage	V _{GS}	0V < V _{DS} < +8V		-3	V
Drain-Source Current	I _{DS}	For V _{DS} > 2V		I _{DSS}	mA
Gate Current	I _G	Forward or reverse current		+15/-2	mA
RF Input Power ²	P _{IN}	Under any acceptable bias state		900	mW
Channel Operating Temperature	T _{CH}	Under any acceptable bias state		175	°C
Storage Temperature	T _{STG}	Non-Operating Storage	-40	150	°C
Total Power Dissipation	P _{TOT}	See De-Rating Note below		8.5	W
Gain Compression	Comp.	Under any bias conditions		5	dB
Simultaneous Combination of Limits ³		2 or more Max. Limits		80	%

¹T_{Ambient} = 22°C unless otherwise noted ²Max. RF Input Limit must be further limited if input VSWR > 2.5:1

³Users should avoid exceeding 80% of 2 or more Limits simultaneously

Notes:

- Operating conditions that exceed the Absolute Maximum Ratings could result in permanent damage to the device.
- Thermal Resistivity specification assumes a Au/Sn eutectic die attach onto a Au-plated copper heatsink or rib.
- Power Dissipation defined as: P_{TOT} ≡ (P_{DC} + P_{IN}) – P_{OUT}, where
 P_{DC}: DC Bias Power
 P_{IN}: RF Input Power
 P_{OUT}: RF Output Power
- Absolute Maximum Power Dissipation to be de-rated as follows above 22°C:
 $P_{TOT} = 8.5W - (0.056W/°C) \times T_{HS}$
 where T_{HS} = heatsink or ambient temperature above 22°C

Example: For a 85°C heatsink temperature: P_{TOT} = 8.5W – (0.056 x (85 – 22)) = 4.9W

• **HANDLING PRECAUTIONS**

To avoid damage to the devices care should be exercised during handling. Proper Electrostatic Discharge (ESD) precautions should be observed at all stages of storage, handling, assembly, and testing. This product has been tested to Class 1A (> 250V but < 500V) using JESD22 A114, Human Body Model, and to Class A, (< 200V) using JESD22 A115, Machine Model..

• **ASSEMBLY INSTRUCTIONS**

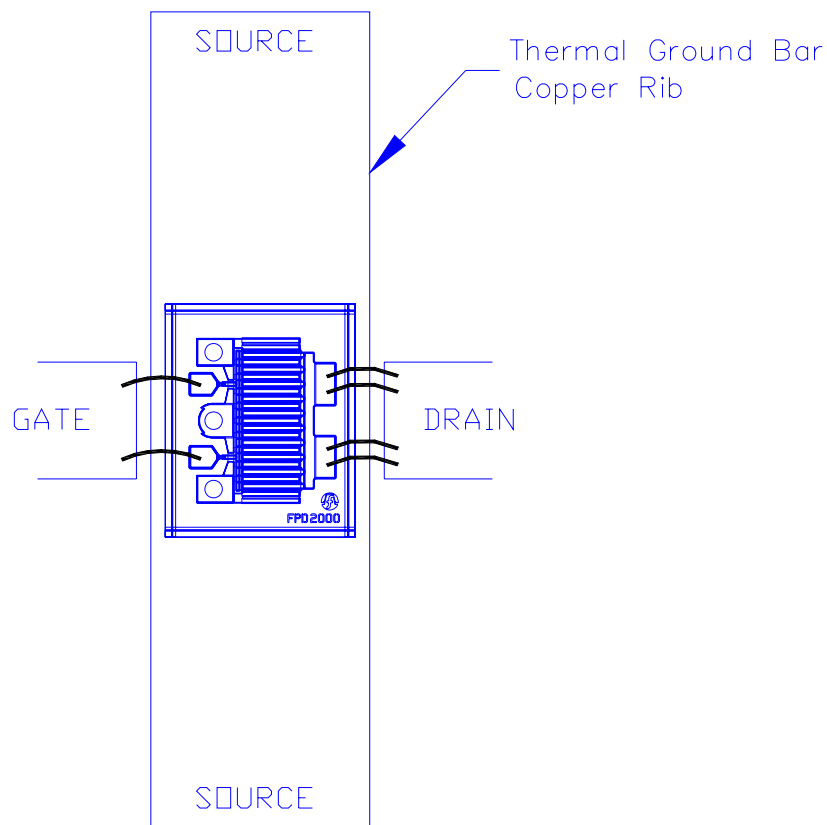
The recommended die attach is gold/tin eutectic solder under a nitrogen atmosphere. Stage temperature should be 280-290°C; maximum time at temperature is one minute. The recommended wire bond method is thermo-compression wedge bonding with 1.0 mil (0.025 mm) gold wire. Stage temperature should be 250-260°C.

- APPLICATIONS NOTES & DESIGN DATA

Applications Notes are available from your local Filtronic Sales Representative or directly from the factory. Complete design data, including S-parameters, noise data, and large-signal models are available on the Filtronic web site.

- BONDING DIAGRAM

Note: 25 μm (0.001 in.) gold wire is recommended. No Source wire bonds are needed, device features Source thru-vias.



All information and specifications are subject to change without notice.